Unitized Semiconductor Devices - Page 1 of 1



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Inclosure Material:

Metal

Overall Length:

0.260 inches

Overall Diameter:

0.370 inches

Component Name And Quantity:

2 transistor

Mounting Method:

Terminal

Semiconductor Material:

Silicon all transistor

Voltage Rating In Volts Per Characteristic:

30.0 collector to base voltage, dc all transistor and 15.0 collector to emitter voltage, dc all transistor and 2.5 emitter to base voltage, dc all transistor

Power Rating Per Characteristic:

720.0 milliwatts small-signal input power, common-collector absolute all transistor

Maximum Operating Tempurature Per Measurement Point:

150.0 degrees celsius junction

Special Features:

All transistor junction pattern arrangement: npn

Test Data Document:

80009-151-0268-00 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing,

etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing)

Terminal Type And Quantity:

6 uninsulated wire lead

Shelf Life:

N/a

Unit Of Measure:

Demilitarization:

No

Fiig:

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